



#### SINGLE P-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
	11mΩ @ V <sub>GS</sub> = -10V	-13A
-30V	17mΩ @ V <sub>GS</sub> = -4.5V	-9.9A

### **Description**

This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(on)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

- Backlighting
- **Power Management Functions**
- DC-DC Converters

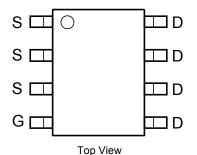
### **Features and Benefits**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

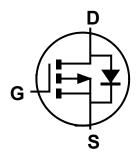
#### Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.074g (approximate)





Internal Schematic



Equivalent circuit

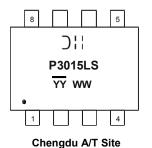
### Ordering Information (Note 4)

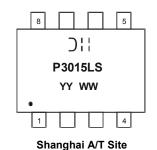
Ī	Part Number	Case	Packaging
	DMP3015LSS-13	SO-8	2500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# Marking Information





);; = Manufacturer's Marking P3015LS = Product Type Marking Code YYWW = Date Code Marking YY or  $\overline{YY}$  = Year (ex: 13 = 2013)

WW = Week (01 - 53)

YY = Date Code Marking for SAT (Shanghai Assembly/ Test site) YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)

DMP3015LSS Document number: DS31472 Rev. 6 - 2

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# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	-30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Drain Current (Note 5)	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-13 -9.75	А
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	-45	Α

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	2.5	W
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	50	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes: 5. Device mounted on 2 oz. Copper pads on FR-4 PCB with  $R_{\theta JA}$  = 50°C/W.

6. Pulse width  $\leq 10 \mu S$ , Duty Cycle  $\leq 1\%$ .

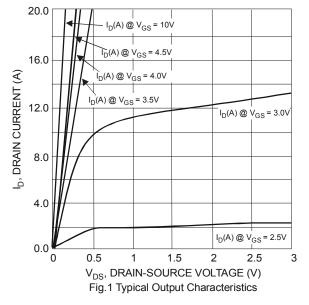
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

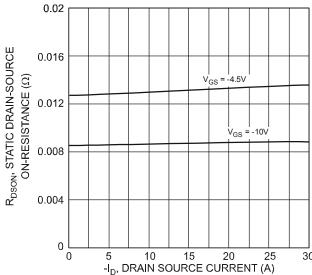
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30			V	$V_{GS} = 0V$ , $I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1	μΑ	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1		-2	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	_	9 14	11 17	mΩ	$V_{GS} = -10V$ , $I_D = -13A$ $V_{GS} = -4.5V$ , $I_D = -10A$	
Forward Transconductance	9fs	_	15	_	S	V <sub>DS</sub> = -15V, I <sub>D</sub> = -8A	
Diode Forward Voltage (Note 7)	$V_{SD}$	-0.5	_	-1.1	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -2.1A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	_	2748	_	pF		
Output Capacitance	Coss	_	357	_	pF	$V_{DS} = -20V, V_{GS} = 0V$	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	356	_	pF	f = 1.0MHz	
Gate Resistance	$R_G$	_	2.0	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ f = 1.0MHz	
SWITCHING CHARACTERISTICS (Note 8)							
Total Gate Charge	Qg	_	30.0 60.4	_		$V_{DS}$ = -10V, $V_{GS}$ = -4.5V, $I_{D}$ = -13A $V_{DS}$ = -10V, $V_{GS}$ = -10V, $I_{D}$ = -13A	
Gate-Source Charge	Qgs	_	7.2	_	nC	V <sub>DS</sub> = -10V, V <sub>GS</sub> = -10V, I <sub>D</sub> = -13A	
Gate-Drain Charge	Q <sub>gd</sub>	_	16.4	_		V <sub>DS</sub> = -10V, V <sub>GS</sub> = -10V, I <sub>D</sub> = -13A	
Turn-On Delay Time	t <sub>d(on)</sub>	_	11.2	_			
Rise Time	t <sub>r</sub>	_	12.4	_			
Turn-Off Delay Time	t <sub>d(off)</sub>	_	104.9		ns	$I_D = -1A, R_G = 6.0\Omega$	
Fall Time	t <sub>f</sub>	_	61.7	_			

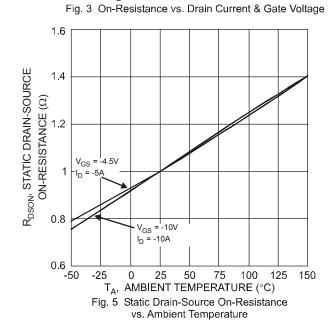
Notes: 7. Short duration pulse test used to minimize self-heating effect.

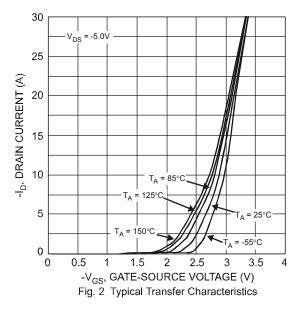
8. Guaranteed by design. Not subject to product testing.











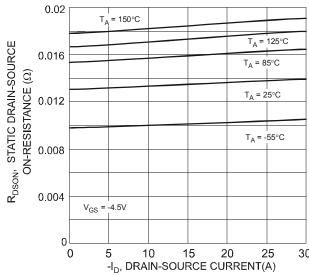
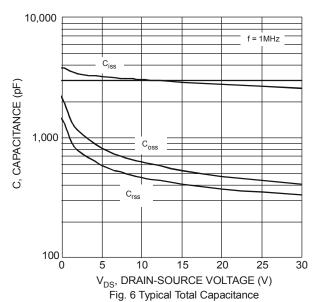


Fig. 4 On-Resistance vs.Drain Current & Gate Voltage





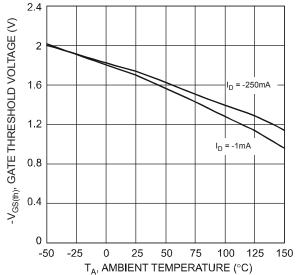


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

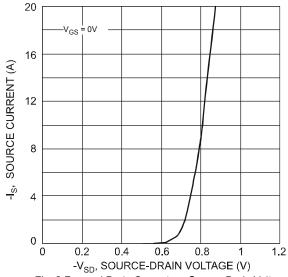
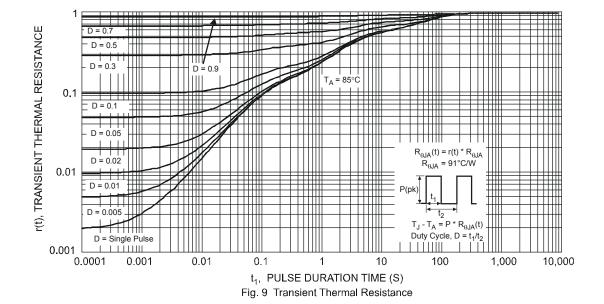
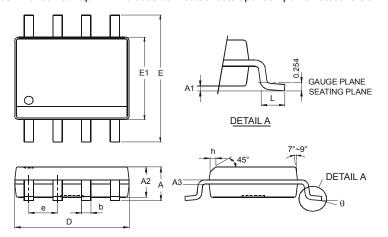


Fig. 8 Forward Drain Current vs. Source-Drain Voltage



# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



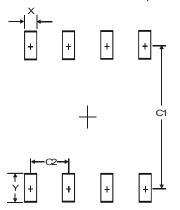
SU-8					
Dim	Min	Max			
Α	_	1.75			
A1	0.08	0.25			
A2	1.30	1.50			
A3	0.20	0.20 Typ.			
b	0.3	0.5			
D	4.80	5.30			
Е	5.79	6.20			
E1	3.70	4.10			
е	1.27 Typ.				
h	_	0.35			
L	0.38	1.27			
θ	0°	8°			
All Dimensions in mm					

SU 8



### Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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